



(19)

(11) Publication number: 05195183 A

Generated Document.

PATENT ABSTRACTS OF JAPAN

(21) Application number: 04010016

(51) Int. Cl.: C23C 2/14 C23C 2/08 C23C 2/10 H01L
21/288

(22) Application date: 23.01.92

(30) Priority:

(43) Date of application publication: 03.08.93

(84) Designated contracting states:

(71) Applicant: MITSUBISHI ELECTRIC CORP

(72) Inventor: SHIMODA HIROSHI

(74) Representative:

(54) PRODUCTION FOR
SEMICONDUCTOR DEVICE

(57) Abstract:

PURPOSE: To shorten a working hour which is long time (about 2 hours) in the conventional method, when producing an electrode for semiconductor element.

CONSTITUTION: A plating solution 5 is blown to a wafer 1, on which the semiconductor element is formed, and when current is applied between a cathode electrode 13 opposite to the wafer 1 and a current regulating anode electrode 8 to form the element electrode, high, low and reverse current are applied repeatedly from a current control type D.C. power source 10.

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